ALPHA & OMEGA SEMICONDUCTOR

AOC2412

20V N-Channel MOSFET

General Description

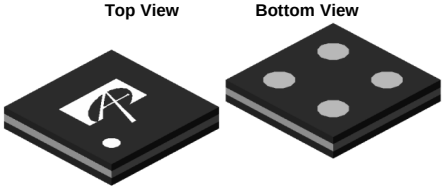
The AOC2412 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V while retaining a 8V $V_{GS(MAX)}$ rating.

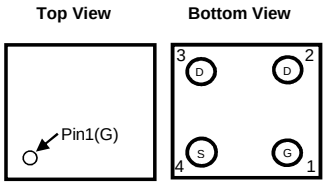
Product Summary

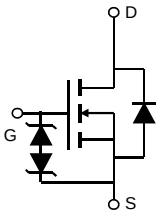
V_{DS}	20V
I_D (at V_{GS}=4.5V)	4.5A
$R_{DS(ON)}$ (at V_{GS}=4.5V)	< 23mΩ
$R_{DS(ON)}$ (at V_{GS}=2.5V)	< 26mΩ
$R_{DS(ON)}$ (at V_{GS}=1.8V)	< 30mΩ
Typical ESD protection	**HBM Class 3A**

Green Product

AlphaDFN 1.57x1.57_4







Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	±8	V
Source Current (DC) Note1	T_A=25°C	I_D	4.5	A
Source Current (Pulse) **Note2**		I_{DM}	65	
Power Dissipation Note1	T_A=25°C	P_D	0.55	W
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient A	t ≤ 10s	$R_{\theta JA}$	140	170	°C/W
Maximum Junction-to-Ambient A D	Steady-State		190	230	°C/W

Note 1. Mounted on minimum pad PCB

Note 2. PW <300 µs pulses, duty cycle 0.5% max

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=20V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±8V			±10	µA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250µA	0.4	0.7	1.0	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=4.5V, I_D=1.5A		18	23	mΩ
		T_J=125°C		22.5	29	
		V_{GS}=2.5V, I_D=1A		20	26	mΩ
		V_{GS}=1.8V, I_D=1A		22	30	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=1.5A		30		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.65	1	V
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=10V, f=1MHz		1842		pF
C_{oss}	Output Capacitance			245		pF
C_{rss}	Reverse Transfer Capacitance			70		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		2.7		KΩ
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=4.5V, V_{DS}=10V, I_D=1.5A		21.5	32	nC
Q_{gs}	Gate Source Charge			10.5		nC
Q_{gd}	Gate Drain Charge			4.5		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=4.5V, V_{DS}=10V, R_L=6.67Ω, R_{GEN}=3Ω		2.5		µs
t_r	Turn-On Rise Time			4		µs
$t_{D(off)}$	Turn-Off DelayTime			5		µs
t_f	Turn-Off Fall Time			8		µs
t_{rr}	Body Diode Reverse Recovery Time	I_F=1.5A, dI/dt=100A/µs		20		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=1.5A, dI/dt=100A/µs		10		nC

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

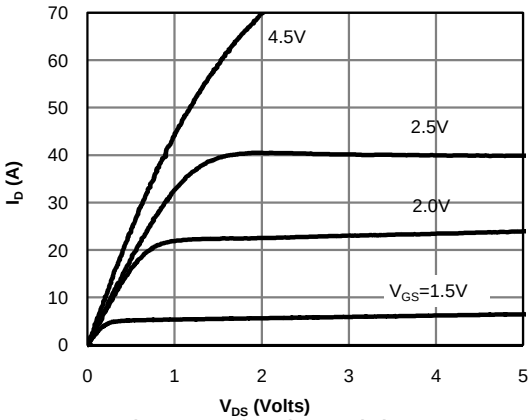


Fig 1: On-Region Characteristics

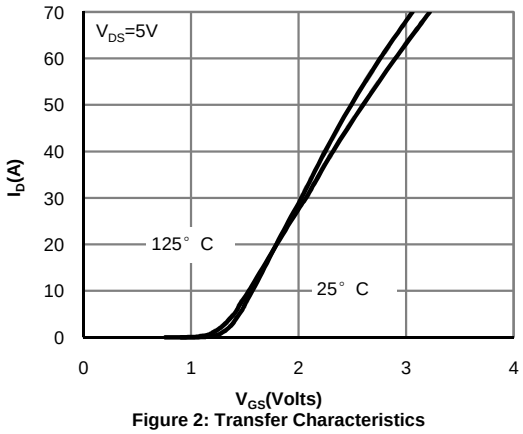


Figure 2: Transfer Characteristics

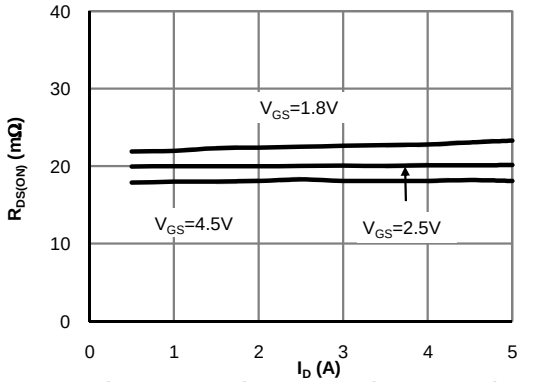


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

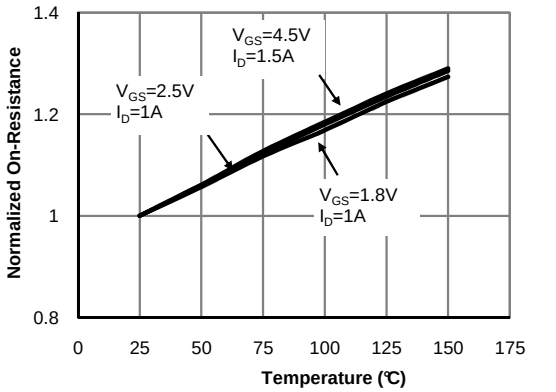


Figure 4: On-Resistance vs. Junction Temperature (Note E)

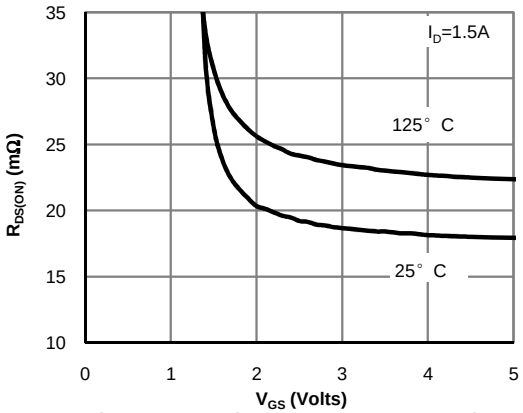


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

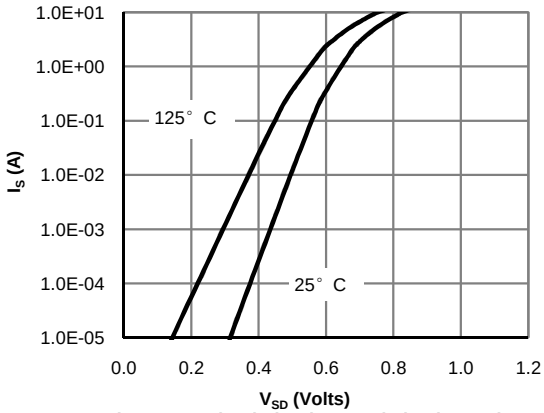


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

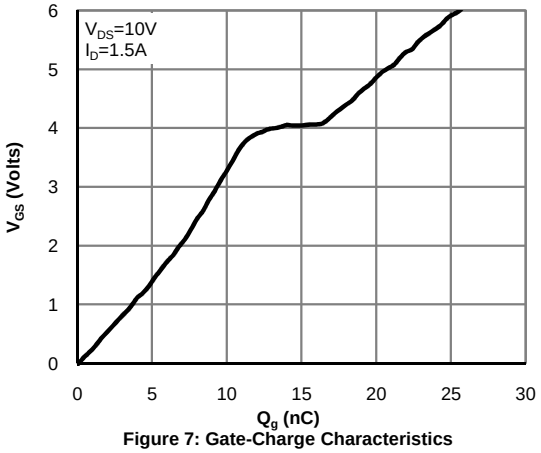


Figure 7: Gate-Charge Characteristics

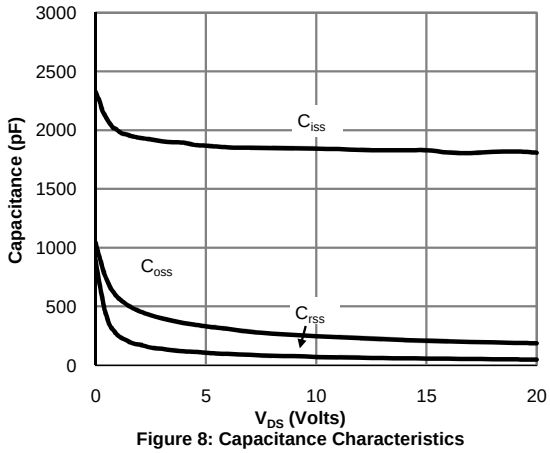


Figure 8: Capacitance Characteristics

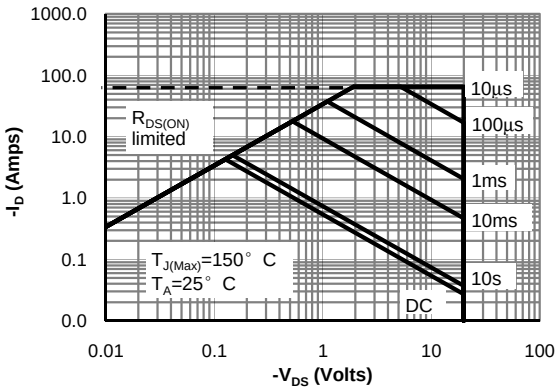


Figure 9: Maximum Forward Biased Safe Operating Area

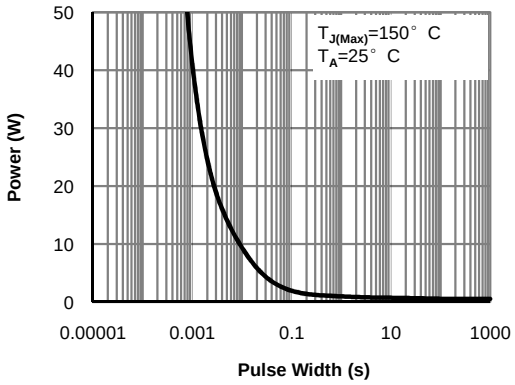


Figure 10: Single Pulse Power Rating Junction-to-Ambient

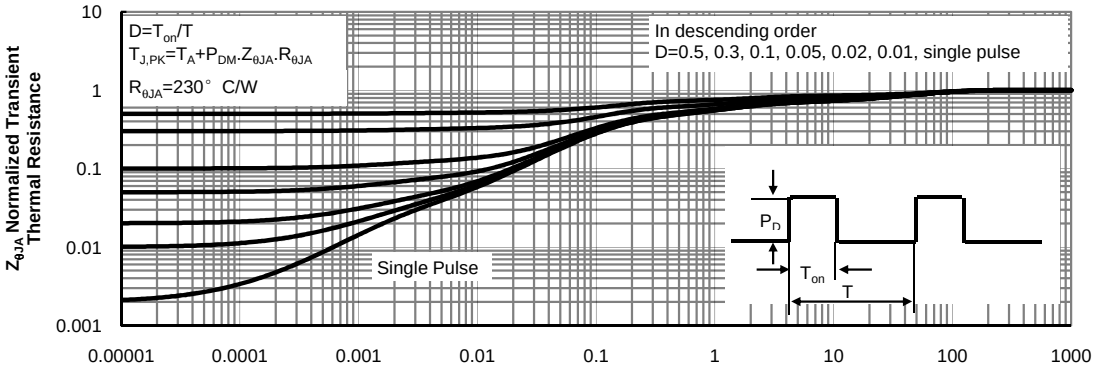
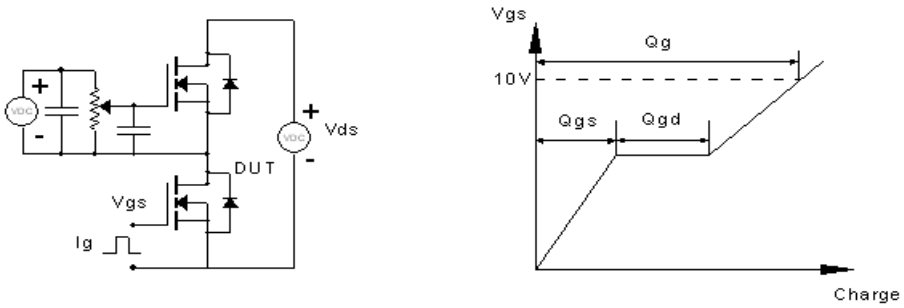
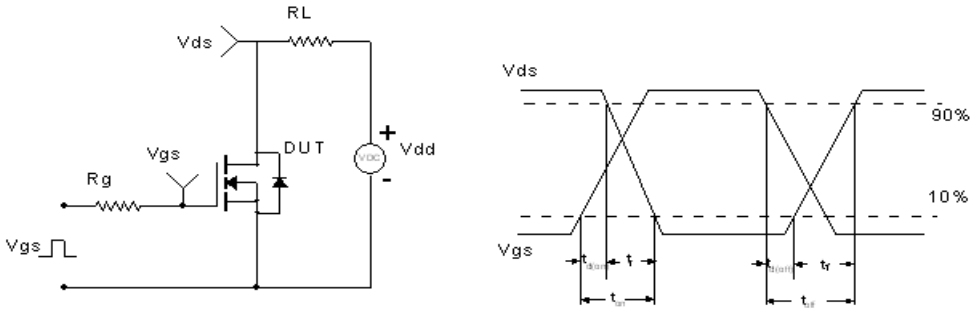


Figure 11: Normalized Maximum Transient Thermal Impedance

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms